









	<h2 style="color: red;">SI3483CDV-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI3483CDV-T1-GE3</p> <hr/> <p>Hersteller / Marke: Vishay / Siliconix</p> <hr/> <p>Teil der Beschreibung: MOSFET P-CH 30V 8A 6-TSOP</p> <hr/> <p>Datenblätter:  SI3483CDV-T1-GE3.pdf</p> <hr/> <p>RoHs Status: Bleifrei / RoHS-konform</p> <hr/> <p>Lagerzustand: New original, 87250 pcs Stock Available.</p> <hr/> <p>Liefern von: Hong Kong</p> <hr/> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI3483CDV-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 30V 8A 6-TSOP
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	87250 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SOT-23-6 Thin, TSOT-23-6
Supplier Device-Gehäuse	6-TSOP
Verlustleistung (max)	2W (Ta), 4.2W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	8A (Tc)
Rds On (Max) @ Id, Vgs	34 mOhm @ 6.1A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	33nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1000pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)

























SI3483CDV-T1-GE3 ist neu im Original, Suche SI3483CDV-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI3483CDV-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI3483CDV-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI3483CDV-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 8A 6-TSOP</p>	 <p>SI3483CDV-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 8A 6-TSOP</p>	 <p>SI3483-A02-GM Energy Micro (Silicon Labs) IC POE PSE 64PORT 24QFN</p>	 <p>SI3483DV-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 4.7A 6-TSOP</p>
 <p>SI3484-A01-GM Energy Micro (Silicon Labs) PSE POWER MANAGEMENT IC</p>	 <p>SI3483CDV-T1-E3 Vishay / Siliconix MOSFET P-CH 30V 8A 6-TSOP</p>	 <p>SI3483-A02-GMR Energy Micro (Silicon Labs) IC POE PSE 64PORT 24QFN</p>	 <p>SI3483DV-T1-E3 Vishay / Siliconix MOSFET P-CH 30V 4.7A 6-TSOP</p>

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 SI3473CDV-T1-GE3	 SI3473DDV-T1-GE3	 SI3473DV-T1-E3	 SI3473DV-T1-E3	 SI3473DV-T1-GE3
 SI3473DV-T1-GE3	 SI3474DV-T1-GE3	 SI3474DV-T1-GE3	 SI3475DV-T1-E3	 SI3475DV-T1-E3
 SI3475DV-T1-GE3	 SI3475DV-T1-GE3	 SI3476DV-T1-E3	 SI3476DV-T1-GE3	 SI3476DV-T1-GE3
 SI3477DV-T1-E3	 SI3477DV-T1-GE3	 SI3477DV-T1-GE3	 SI3481DV-T1-E3	 SI3481DV-T1-E3
 SI3481DV-T1-GE3	 SI3481DV-T1-GE3	 SI3483CDV-T1-E3	 SI3483CDV-T1-E3	 SI3483CDV-T1-GE3
 SI3483DV-T1-E3	 SI3483DV-T1-E3	 SI3483DV-T1-GE3	 SI3483DV-T1-GE3	 SI3493BDV-T1-E3
 SI3493BDV-T1-E3	 SI3493BDV-T1-E3-S	 SI3493BDV-T1-GE3	 SI3493BDV-T1-GE3	 SI3493DDV-T1-GE3
 SI3493DDV-T1-GE3	 SI3493DV	 SI3493DV-T1	 SI3493DV-T1-E3	 SI3493DV-T1-E3
 SI3493DV-T1-E3	 SI3493DV-T1-GE3	 SI3493DV-T1-GE3	 SI3495DV	 SI3495DV-T1-E3
 SI3495DV-T1-E3	 SI3495DV-T1-GE3	 SI3495DV-T1-GE3	 SI3499DV-T1-E3	 SI3499DV-T1-E3

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